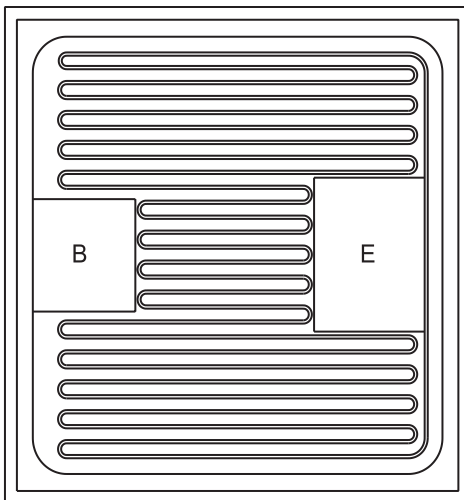


PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	41.3 x 41.3 MILS
Die Thickness	9.0 MILS
Base Bonding Pad Area	9.5 x 9.2 MILS
Emitter Bonding Pad Area	12.8 x 10.2 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au - 18,000Å

GEOMETRY

BACKSIDE COLLECTOR

R0

GROSS DIE PER 4 INCH WAFER

6,670

PRINCIPAL DEVICE TYPES

CMPT3090L

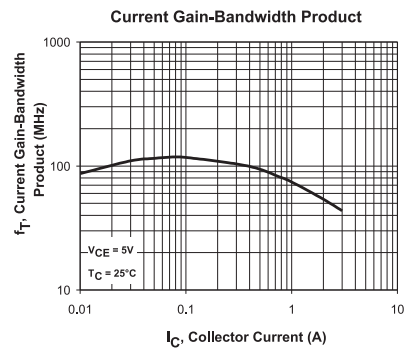
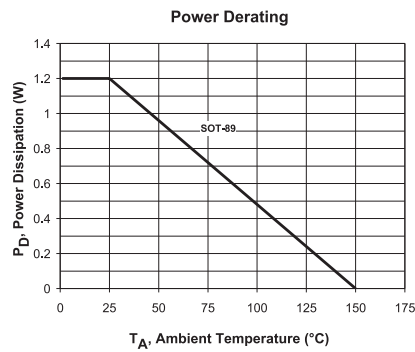
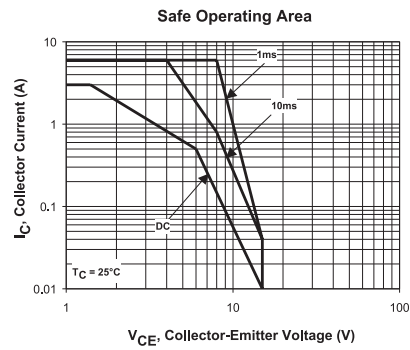
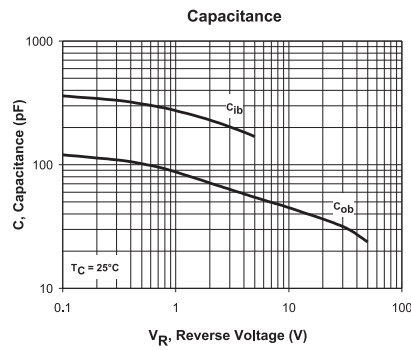
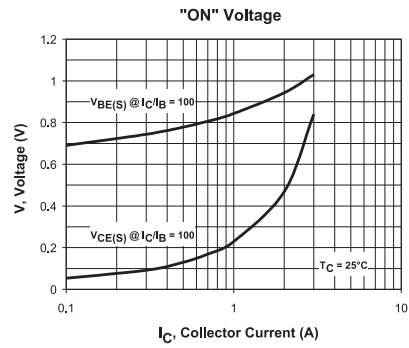
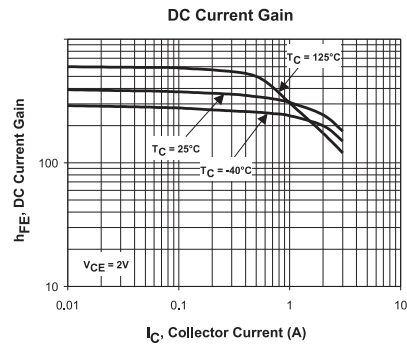
CXT3090L

CZT3090L

CMXT3090L

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